

isc N-Channel MOSFET Transistor

IRFP150M, IIRFP150M

FEATURES

- Static drain-source on-resistance:
 R_{DS}(on)≤36mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

- · Fast switching
- Fully Avalanche Rated

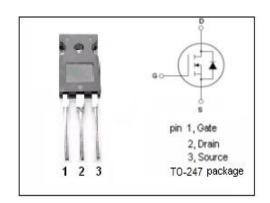


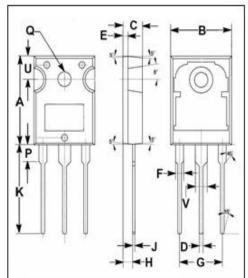
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	42	А
I _{DM}	Drain Current-Single Pulsed	140	А
P _D	Total Dissipation @T _C =25°C	160	W
Tj	Max. Operating Junction Temperature	175	$^{\circ}$ C
T _{stg}	Storage Temperature	-55~175	${\mathbb C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.95	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	40	°C/W





DIM MIN I	XAN
A 19.80 2	0.20
B 15.40 1	5.80
C 4.90	5.10
D 0.90	1.10
E 1.40	1.60
F 1.90	2.10
G 10.80 1	1.00
H 2.40	2.60
J 0.50	0.70
K 19.50 2	0.50
P 3.90	4.10
Q 3.30	3.50
U 5.20	5.40
V 2.90	3.10

mm



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =250 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =23A			36	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μ A
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			25	μ А
V _{SD}	Diode forward voltage	I _S =23A, V _{GS} = 0V			1.3	V

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